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Takagi

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(54) **MILLIMETER WAVE BANDS
SEMICONDUCTOR PACKAGE**

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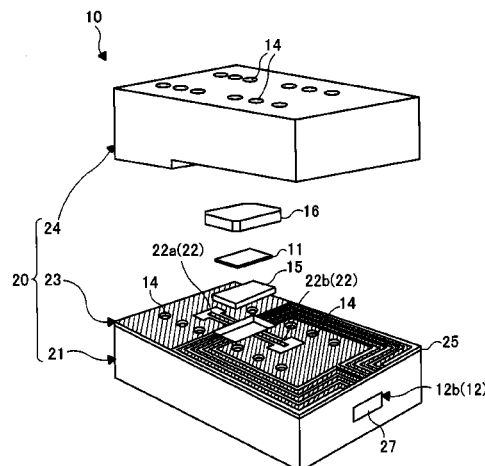
(57) **ABSTRACT**

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A millimeter wave bands semiconductor package includes a metal base body, a circuit board, and a metal cover body. The base body has a first penetration hole and a second penetration hole. The circuit board is disposed on the base body and has an input signal line and an output signal line on a front side surface thereof. The cover body is disposed on the circuit board and has a first non-penetration hole and a second non-penetration hole. The cover body is disposed such that the first non-penetration hole is disposed directly above the first penetration hole of the base body and the second non-penetration hole is disposed directly above the second penetration hole of the base body. Further, the first non-penetration hole and the first penetration hole constitute a first waveguide and the second non-penetration hole and the second penetration hole constitute a second waveguide.

(58) **Field of Classification Search**
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See application file for complete search history.

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FIG. 1

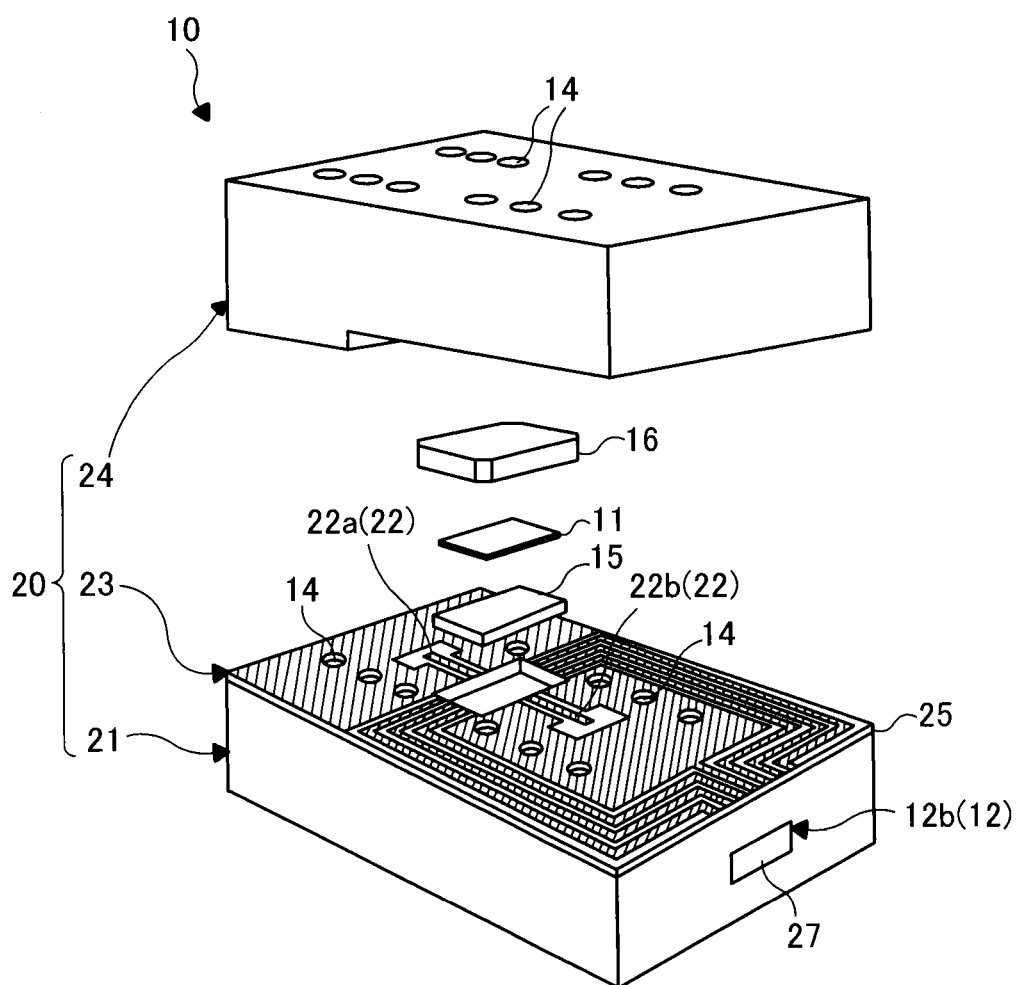


FIG. 2

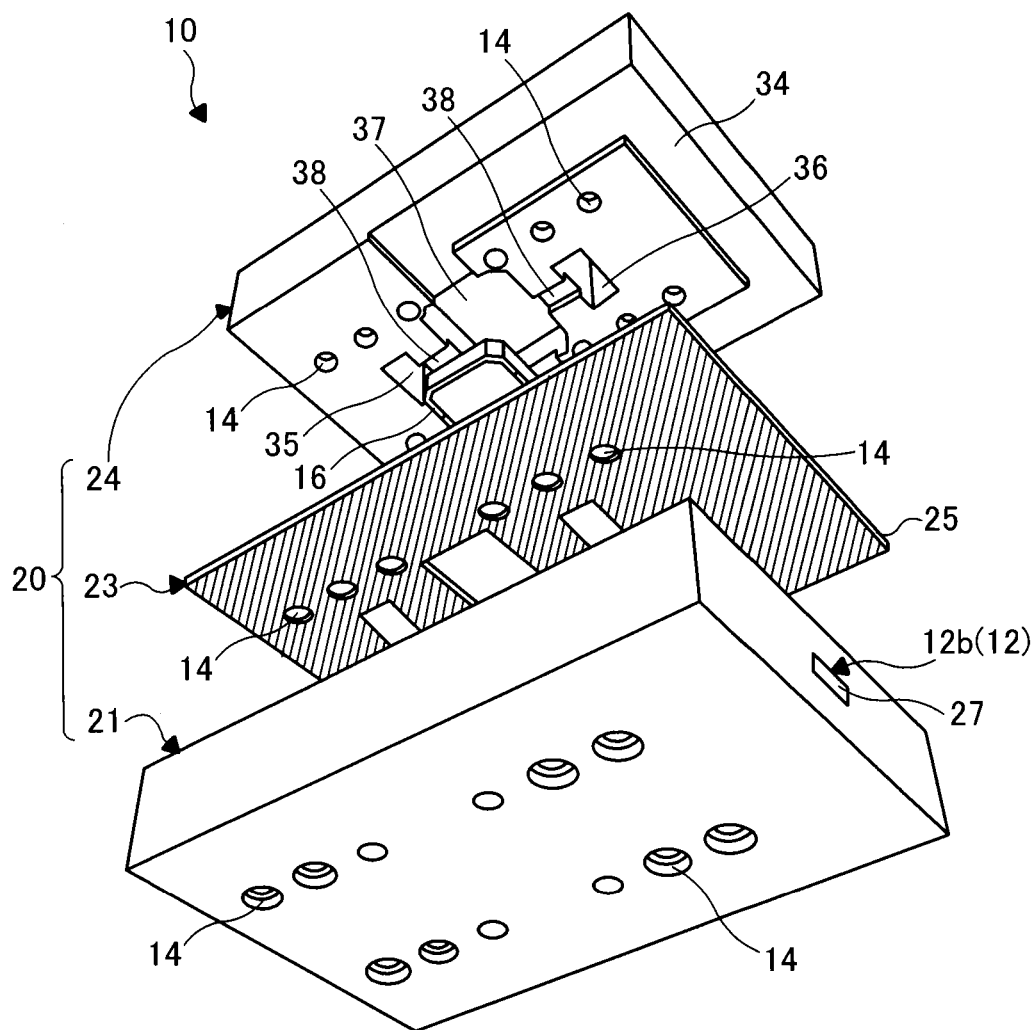


FIG. 3A

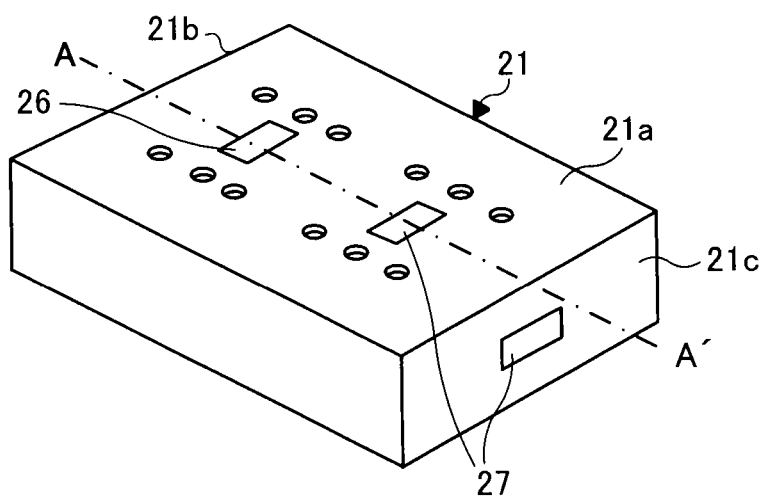


FIG. 3B

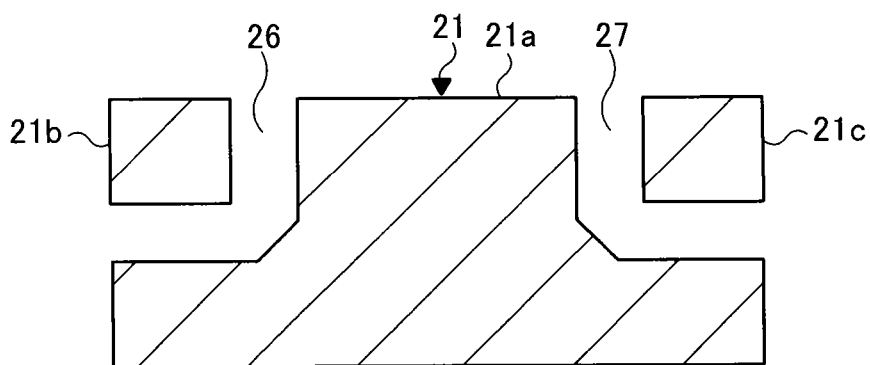


FIG. 4A

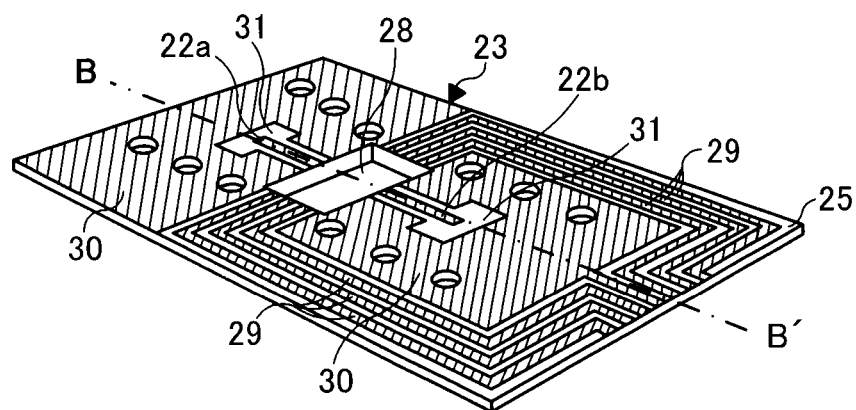


FIG. 4B

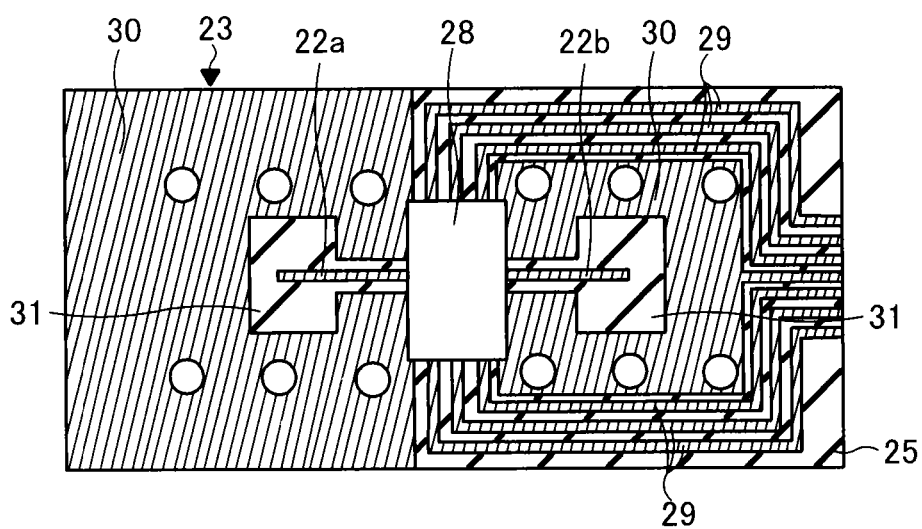


FIG. 4C

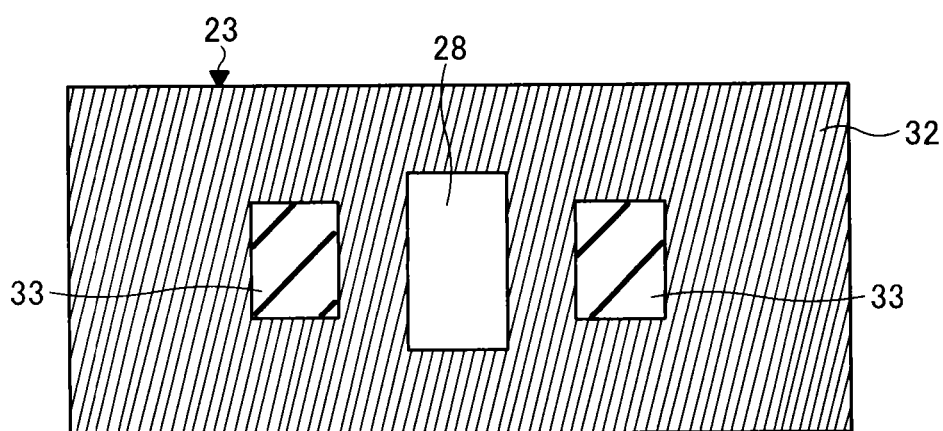


FIG. 4D

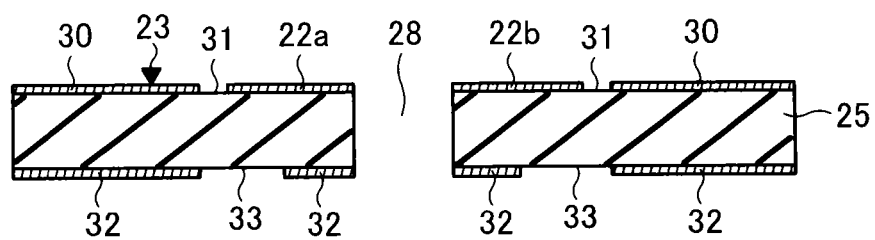


FIG. 5A

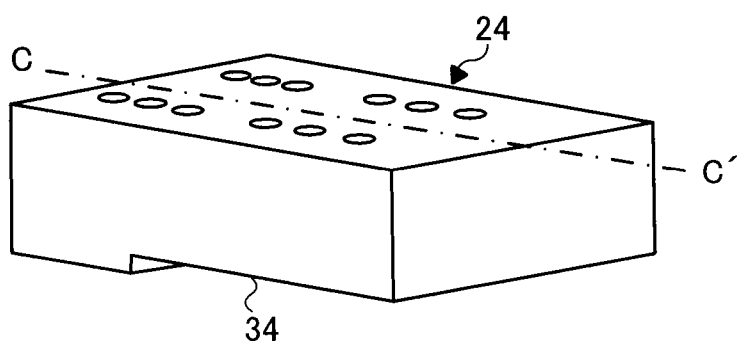


FIG. 5B

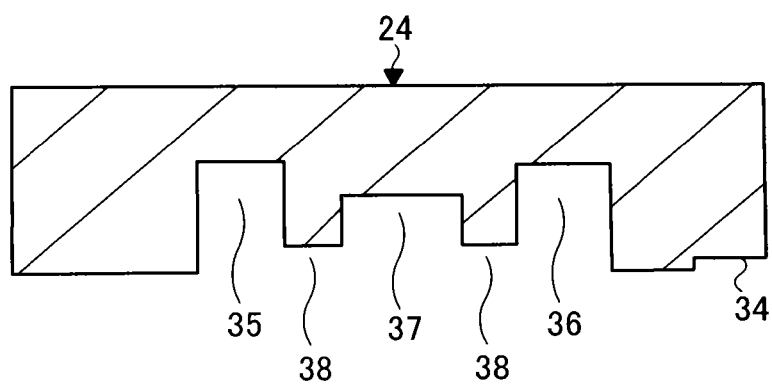
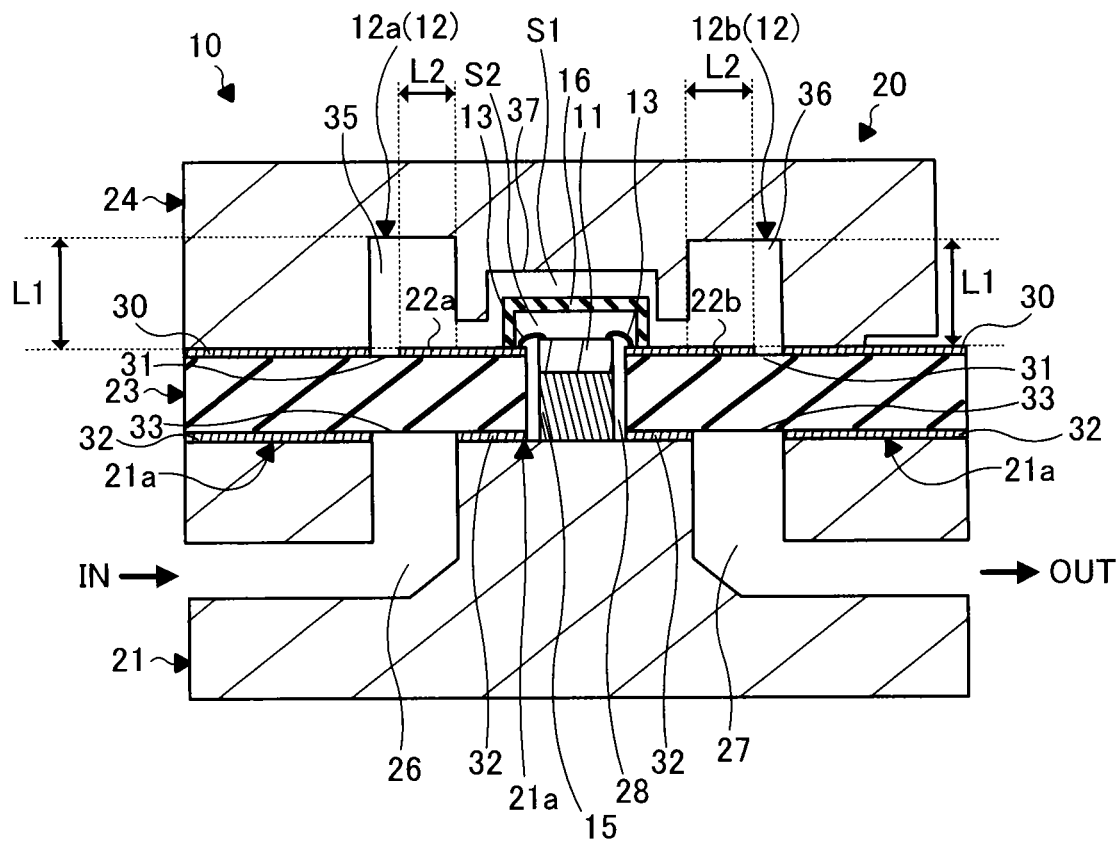


FIG. 6



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MILLIMETER WAVE BANDS SEMICONDUCTOR PACKAGE

CROSS REFERENCE TO RELATED APPLICATIONS

This application is based upon and claims the benefit of priority from the prior Japanese Patent Application No. 2014-022066 filed in Japan on Feb. 7, 2014; the entire contents of which are incorporated herein by reference.

FIELD

Embodiments described herein relate generally to a millimeter wave bands semiconductor package and a millimeter wave bands semiconductor device.

BACKGROUND

A conventional millimeter wave bands semiconductor package, on which a semiconductor chip operating in such a millimeter wave bands of 30 GHz or higher is mounted, includes a base body on which the semiconductor chip is placed, a signal line in which one end thereof is connected to the semiconductor chip and the other end acts as an antenna, and a cover body which is provided on the base body to cover the semiconductor chip. Such a conventional millimeter wave bands semiconductor package is used by inserting the signal line into a waveguide which is connected to an external electrical circuit or the like.

However, the conventional millimeter wave bands semiconductor package which was disclosed in Japan Patent Number 3485520 has two waveguide blocks for an input terminal antenna and an output terminal antenna. Since the two waveguide blocks are separate components, the installation states of the waveguide blocks for the antennas are changed at each terminal antenna. Accordingly, there is a problem in that the millimeter wave bands semiconductor package and a millimeter wave bands semiconductor device in which the semiconductor chip is mounted on the package are poor in reproducibility.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is an exploded perspective view illustrating schematically a millimeter wave bands semiconductor device according to embodiments when viewed obliquely from above;

FIG. 2 is an exploded perspective view illustrating schematically the millimeter wave bands semiconductor device according to embodiments when viewed obliquely from below;

FIG. 3A is a perspective view illustrating schematically a base body of a millimeter wave bands semiconductor package according to embodiments when viewed obliquely from above;

FIG. 3B is a cross-sectional view illustrating schematically the base body taken along the dashed-dotted line A-A' in FIG. 3A;

FIG. 4A is a perspective view illustrating schematically a circuit board of the millimeter wave bands semiconductor package according to embodiments when viewed obliquely from above;

FIG. 4B is a plan view illustrating schematically the circuit board of the millimeter wave bands semiconductor package according to embodiments when viewed obliquely from above;

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FIG. 4C is a plan view illustrating schematically the circuit board of the millimeter wave bands semiconductor package according to embodiments when viewed obliquely from below;

FIG. 4D is a cross-sectional view illustrating schematically the circuit board taken along the dashed-dotted line B-B' in FIG. 4A;

FIG. 5A is a perspective view illustrating schematically a cover body of the millimeter wave bands semiconductor package according to embodiments when viewed obliquely from above;

FIG. 5B is a cross-sectional view illustrating schematically the cover body taken along the dashed-dotted line C-C' in FIG. 5A; and

FIG. 6 is a cross-sectional view corresponding to FIGS. 3B, 4D, and 5B illustrating the millimeter wave bands semiconductor device according to embodiments.

DESCRIPTION OF THE EMBODIMENTS

Certain embodiments provide a millimeter wave bands semiconductor package including a metal base body, a circuit board, and a metal cover body. The base body has a first penetration hole and a second penetration hole. The circuit board is disposed on the base body and has an input signal line and an output signal line on a front side surface thereof. The cover body is disposed on the circuit board and has a first non-penetration hole and a second non-penetration hole. The cover body is disposed on the circuit board such that the first non-penetration hole is disposed directly above the first penetration hole of the base body and the second non-penetration hole is disposed directly above the second penetration hole of the base body. Further, the first non-penetration hole and the first penetration hole constitute a first waveguide and the second non-penetration hole and the second penetration hole constitute a second waveguide.

Certain embodiments provide a millimeter wave bands semiconductor device including a metal base body, a circuit board, a metal cover body, and a semiconductor chip. The base body has a first penetration hole and a second penetration hole. The circuit board is disposed on the base body and has an input signal line and an output signal line on a front side surface of the circuit board. The circuit board has a penetration hole in a part thereof. The cover body is disposed on the circuit board and has a first non-penetration hole and a second non-penetration hole. The cover body is disposed on the circuit board such that the first non-penetration hole is disposed directly above the first penetration hole of the base body and the second non-penetration hole is disposed directly above the second penetration hole of the base body. Further, the first non-penetration hole and the first penetration hole constitute a first waveguide and the second non-penetration hole and the second penetration hole constitute a second waveguide. The semiconductor chip is placed on a front side surface of the base body so as to be disposed in the penetration hole of the circuit board and is electrically connected to the input signal line and the output signal line.

A millimeter wave bands semiconductor package and a millimeter wave bands semiconductor device according to embodiments will be described below.

FIG. 1 is an exploded perspective view illustrating schematically a millimeter wave bands semiconductor device according to embodiments when viewed obliquely from above. In addition, FIG. 2 is an exploded perspective view illustrating schematically the millimeter wave bands semiconductor device according to embodiments when viewed obliquely from below. As illustrated in FIGS. 1 and 2, in a

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millimeter wave bands semiconductor device **10** according to the embodiments, a semiconductor chip **11** is mounted inside a millimeter wave bands semiconductor package **20**. The millimeter wave bands semiconductor package **20** includes a base body **21**, a circuit board **23** provided with signal lines **22** and the like, and a cover body **24**.

Each of the base body **21** and the cover body **24** included in the millimeter wave bands semiconductor package **20** is a cuboid metal block. Further, the circuit board **23** is configured such that a desired circuit pattern or the like is formed on a front side surface of a dielectric substrate **25** and a desired pattern is also formed on a back side surface of the dielectric substrate **25**.

Such a millimeter wave bands semiconductor package **20** will be described in detail below.

FIG. 3A is a perspective view illustrating schematically the base body **21** of the millimeter wave bands semiconductor package **20** according to the embodiment when viewed obliquely from above. In addition, FIG. 3B is a cross-sectional view illustrating schematically the base body **21** taken along the dashed-dotted line A-A' in FIG. 3A.

As illustrated in FIGS. 3A and 3B, each of a first penetration hole **26** and a second penetration hole **27** bending into L-shaped is provided in the cuboid base body **21** as the metal block to penetrate the base body **21** toward side surfaces **21b** and **21c** from a front side surface **21a**. The first penetration hole **26** penetrates the base body **21** toward the first side surface **21b** from the front side surface **21a**, and the second penetration hole **27** penetrates the base body **21** toward the second side surface **21c** opposite to the first side surface **21b** from the front side surface **21a**. Each of the penetration holes **26** and **27** constitutes waveguides **12**, through which millimeter waves are guided, together with non-penetration holes **35** and **36** of the cover body **24** which will be described below.

As illustrated in FIG. 3A, each of the penetration holes **26** and **27** is a penetration hole of a so-called E-plane bend type having a horizontally long shape in cross section, but each of the penetration holes **26** and **27** may be a penetration hole of a so-called H-plane bend type having a vertical long shape in cross section. However, when each of the penetration holes **26** and **27** is formed in the H-plane bend type, the base body **21** becomes thicker. Accordingly, it is preferable that each of the penetration holes **26** and **27** is the penetration hole of the so-called E-plane bend type, as illustrated in FIG. 3A.

In addition, the base body **21** may be made of a metal, but is preferably made of a metal such as Cu having excellent heat conductivity in order to improve radiation performance of heat emitted from the semiconductor chip **11** (see FIGS. 1 and 2) mounted on the front side surface **21a** of the base body **21**.

FIG. 4A is a perspective view illustrating schematically the circuit board **23** of the millimeter wave bands semiconductor package **20** according to the embodiment when viewed obliquely from above, FIG. 4B is a plan view illustrating schematically the circuit board **23** when viewed obliquely from above, FIG. 4C is a plan view illustrating schematically the circuit board **23** when viewed obliquely from below, and FIG. 4D is a cross-sectional view illustrating schematically the circuit board **23** taken along the dashed-dotted line B-B' in FIG. 4A.

As illustrated in FIGS. 4A to 4D, the circuit board **23** is configured such that a desired circuit pattern or the like is formed on the front side surface of the dielectric substrate **25** and a desired pattern is also formed on the back side surface of the dielectric substrate **25**.

The dielectric substrate **25** is formed of, for example, ceramic or the like in a plate shape, and a substantially rectangular penetration hole **28** is provided in a substantially

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central region of the dielectric substrate **25** to dispose the semiconductor chip **11** or the like.

As illustrated in FIGS. 4A, 4B, and 4D, a circuit pattern including input/output signal lines **22a** and **22b**, a plurality of bias supplying lines **29**, and a first ground pattern **30** is provided on the front side surface of the dielectric substrate **25** by a metal thin film, for example, Cu or the like.

The input signal line **22a** extends by a predetermined distance toward one side of the dielectric substrate **25** from a long side of the substantially rectangular penetration hole **28**, on the front side surface of the dielectric substrate **25**. One end of the input signal line **22a** receives millimeter waves guided through the waveguide **12** which will be described below. In addition, the other end of the input signal line **22a** guides the received millimeter waves to the semiconductor chip **11** which is electrically connected to the other end.

The output signal line **22b** extends by a predetermined distance toward a direction opposite to the extending direction of the input signal line **22a** from along side of the penetration hole **28** facing the long side which comes in contact with the input signal line **22a**, on the front side surface of the dielectric substrate **25**. One end of the output signal line **22b** receives the millimeter waves guided from the semiconductor chip **11** which is electrically connected to the one end. In addition, the other end of the output signal line **22b** transmits the received millimeter waves to the waveguide **12**.

Accordingly, the predetermined distances of the input signal line **22a** and the output signal line **22b** refer to a distance longer than the lengths of these signal lines **22a** and **22b** which are capable of acting as a monopole antenna for transmitting and receiving the millimeter waves guided through the waveguide **12**, respectively.

Each of the plurality of bias supplying lines elongates along a peripheral portion of the dielectric substrate **25** from, for example, a short side of the substantially rectangular penetration hole **28** and extends to come in contact with one side of the dielectric substrate **25**, respectively, on the front side surface of the dielectric substrate **25**. These bias supplying lines **29** are lines to supply a DC bias to the semiconductor chip **11**, respectively.

The first ground pattern **30** is provided on the approximately entire front side surface of dielectric substrate **25** so as to be insulated from the input signal line **22a**, the output signal line **22b**, and the plurality of bias supplying lines **29**. The first ground pattern **30** is removed in a substantially rectangular shape in the vicinity of one end of the input signal line **22a**, and the first ground pattern **30** is removed in a substantially rectangular shape in the vicinity of the other end of the output signal line **22b**.

Further, the substantially rectangular front side region of the dielectric substrate **25**, which is exposed by the removal of the ground pattern **30** in this manner, is a region included in the waveguide to be described below. Therefore, the substantially rectangular front side region of the dielectric substrate **25**, which is exposed by the removal of the first ground pattern **30**, is referred to as a front side waveguide region **31**.

Next, as illustrated in FIGS. 4C and 4D, a second ground pattern **32** is provided on the back side surface of the dielectric substrate **25** by a metal thin film, for example, Cu or the like. The second ground pattern **32** is provided on the approximately entire back side surface of the dielectric substrate **25**, but the region corresponding to the front side waveguide regions **31** is removed. The ground pattern **30** and the ground pattern **32** are electrically connected to each other by a plurality of through holes (not illustrated in the drawings).

Further, similar to the front side region, the substantially rectangular back side region of the dielectric substrate **25**,

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which is exposed by the removal of the ground pattern 32 in this manner, is also a region included in the waveguide 12 to be described below. Therefore, the substantially rectangular back side region of the dielectric substrate 25, which is exposed by the removal of the second ground pattern 32, is referred to as a back side waveguide region 33.

FIG. 5A is a perspective view illustrating schematically the cover body 24 of the millimeter wavebands semiconductor package 20 according to the embodiments when viewed obliquely from above. In addition, FIG. 5B is a cross-sectional view illustrating schematically the cover body taken along the dashed-dotted line C-C' in FIG. 5A.

The cuboid cover body 24 as the metal block is disposed on the above-described circuit board 23, but, as illustrated in FIGS. 5A, 5B, and 2, respectively, a ring-shaped region 34, which faces the bias supplying line 29, of the back side surface of the cover body 24 is shallowly hollowed out to suppress the contact between the cover body 24 and the bias supplying line 29.

As illustrated in FIGS. 5B and 2, a first non-penetration hole 35 and a second non-penetration hole 36 are provided in the cover body 24 having such a ring-shaped region 34, respectively.

The first non-penetration hole 35 and the second non-penetration hole 36 extend by a predetermined distance toward the front side surface from the back side surface and are provided so as not to penetrate the cover body 24, respectively. As described above, the non-penetration holes 35 and 36 constitute the waveguide 12, through which millimeter waves are guided, together with the penetration holes 26 and 27 of the base body 21, respectively.

Further, the predetermined distances of the first non-penetration hole 35 and the second non-penetration hole 36 refer to such a distance that a distance L1 (see FIG. 6) from the front side surface of the circuit board 23 to the bottom surface of the non-penetration holes 35 and 36 becomes $\lambda/4$ (where λ is a wavelength of the millimeter wave to be used) when the cover body 24 is placed on the circuit board 23.

Further, as illustrated in FIGS. 5B and 2, in the back side surface of the cover body 24, a first recessed portion 37 is provided between the first non-penetration hole 35 and the second non-penetration hole 36 such that the semiconductor chip 11 is disposed and a second recessed portion 38 is provided such that each of the non-penetration holes 35 and 36 is connected to the first recessed portion 37.

FIG. 6 is a cross-sectional view corresponding to FIGS. 3B, 4D, and 5B illustrating the millimeter wave bands semiconductor device 10 in which the semiconductor chip 11 is mounted on the above-described millimeter wavebands semiconductor package 20.

As illustrated in FIG. 6, the circuit board 23 is mounted on the front side surface 21a of the base body 21 such that the back side waveguide regions 33 provided in the back side surface of the circuit board 23 are disposed on a top of the first penetration hole 26 and a top of the second penetration hole 27 of the base body 21 and the second ground pattern 32 on the back side surface of the circuit board 23 comes in contact with the front side surface 21a of the base body 21. In addition, the cover body 24 is mounted on the circuit board 23 such that the first non-penetration hole 35 and the second non-penetration hole 36 are disposed on the front side waveguide regions 31 of the circuit board 23 and the back side surface thereof comes in contact with the first ground pattern 30 on the front side surface of the circuit board 23.

Then, as illustrated in FIGS. 1 and 2, screw holes 14 are provided to penetrate through each of the base body 21, the circuit board 23, and the cover body 24, and the base body 21,

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the circuit board 23, and the cover body 24 are fixed to each other by insertion of fixing screws into these screw holes 14.

In the millimeter wave bands semiconductor package 20 configured in this manner, the first penetration hole 26 of the base body 21 and the first non-penetration hole 35 of the cover body 24 constitute the first waveguide 12a including the front side waveguide region 31 and the back side waveguide region 33 of the circuit board 23 therein. Similarly, the second penetration hole 27 of the base body 21 and the second non-penetration hole 36 of the cover body 24 constitute the second waveguide 12b including the front side waveguide region 31 and the back side waveguide region 33 of the circuit board therein.

Further, in the millimeter wave bands semiconductor package 20 configured in this manner, the input/output signal lines 22a and 22b of the circuit board 23 are in a state of being inserted into these waveguides 12a and 12b by $L2=\lambda/4$ (where λ is a wavelength of the millimeter wave to be used), respectively, to act as a monopole antenna.

The semiconductor chip 11 operating in the millimeter wave is mounted in the above-described millimeter wave bands semiconductor package 20. The semiconductor chip 11 is, for example, a field effect transistor (FET) which amplifies power of the millimeter waves.

The semiconductor chip 11 is mounted on the front side surface of the base body 21 via a metal chip mount plate 15. The semiconductor chip 11 is placed on the front side surface of the base body 21 together with the chip mount plate 15 so as to be disposed in a space S1 which is surrounded substantially by the front side surface of the base plate 21, the side surface of the penetration hole 28 of the circuit board 23, and the first recessed portion 37 of the cover body 24.

Further, a recessed chip cover body 16 formed of, for example, a dielectric material such as ceramic is disposed in the first recessed portion 37 of the cover body 24. Accordingly, in more detail, the semiconductor chip 11 is placed on the front side surface of the base body 21 together with the chip mount plate 15 so as to be disposed in a space S2 which is surrounded substantially by the front side surface of the base plate 21, the side surface of the penetration hole 28 of the circuit board 23, and the chip cover body 16.

The semiconductor chip 11 placed in this manner is electrically connected to the other end of the input signal line 22a of the circuit board 23 by a connection conductor, for example, a wire 13 or the like and is also electrically connected to one end of the output signal line 22b of the circuit board 23 by the connection conductor, for example, the wire 13 or the like.

In the millimeter wave bands semiconductor device 10 in which the semiconductor chip 11 is mounted in the millimeter wave bands semiconductor package 20 in this manner, when the millimeter waves are input into the first waveguide 12a from an arrow IN direction in FIG. 6, the millimeter waves are guided through the first waveguide 12a and received at the input signal line 22a which is inserted and disposed within the first waveguide 12a.

The received millimeter waves are input to the semiconductor chip 11 via the input signal line 22a and are subjected to the desired signal processing (for example, power amplification) in the semiconductor chip 11.

When the signal-processed millimeter waves are output to the output signal line 22b from the semiconductor chip 11, the millimeter waves are transmitted into the second waveguide 12b from the output signal line 22b. The millimeter waves transmitted into the second waveguide 12b are guided through the second waveguide 12b and are output to an arrow OUT direction in FIG. 6.

According to the millimeter wave bands semiconductor package **20** and the millimeter wave bands semiconductor device **10** of the embodiments described above, since the waveguides **12a** and **12b**, through which the millimeter waves are guided, are embedded in the millimeter wave bands semiconductor package **20**, it is possible to provide the millimeter wave bands semiconductor package **20** and the millimeter wave bands semiconductor device **10** in which, for example, a change in relative position between the input/output signal lines **22a** and **22b** and the waveguides **12a** and **12b** is suppressed and reproducibility is excellent.

When the relative position between the input/output signal lines **22a** and **22b** and the waveguides **12a** and **12b** is shifted by, for example, 0.5 mm, the power loss of the millimeter waves is about 3 dB (about half). Accordingly, the excellent reproducibility and, for example, the arrangement of the input/output signal lines **22a** and **22b** with high accuracy at a desired position of the waveguides **12a** and **12b** are very important in the millimeter wave bands semiconductor package **20** and the millimeter wave bands semiconductor device **10**.

Further, according to the millimeter wave bands semiconductor package **20** and the millimeter wave bands semiconductor device **10** of the embodiments described above, the first and second penetration holes **26** and **27**, which are provided in the base body **21** to constitute the waveguides **12a** and **12b** as a main body, penetrate the base body **21** toward the side surfaces **21b** and **21c** from the front side surface **21a**. Accordingly, the back side surface of the base body **21** can be fixed to a cooling mechanism such as a heat radiation fin. As a result, the heat radiation property can be improved.

While certain embodiments have been described, these embodiments have been presented by way of example only, and are not intended to limit the scope of the inventions. Indeed, the novel embodiments described herein may be embodied in a variety of other forms; furthermore, various omissions, substitutions and changes in the form of the embodiments described herein may be made without departing from the spirit of the inventions. The accompanying claims and their equivalents are intended to cover such forms or modifications as would fall within the scope and spirit of the inventions.

What is claimed is:

1. A millimeter wave bands semiconductor package comprising:

- a metal base body having a first penetration hole and a second penetration hole;
- a circuit board that is disposed on the metal base body and that has an input signal line and an output signal line on a front side surface thereof; and
- a metal cover body that is disposed on the circuit board and has a first non-penetration hole and a second non-penetration hole,

wherein the metal cover body is disposed on the circuit board such that the first non-penetration hole is disposed directly above the first penetration hole of the metal base

body and the second non-penetration hole is disposed directly above the second penetration hole of the metal base body, and

the first non-penetration hole and the first penetration hole constitute a first waveguide and the second non-penetration hole and the second penetration hole constitute a second waveguide.

2. The millimeter wave bands semiconductor package according to claim 1, wherein each of the first penetration hole and the second penetration hole of the metal base body is a penetration hole bending into L-shaped which penetrates the metal base body toward a side surface from a front side surface.

3. The millimeter wave bands semiconductor package according to claim 2, wherein each of the first penetration hole and the second penetration hole of the metal base body is a penetration hole of an E-plane bend type.

4. The millimeter wave bands semiconductor package according to claim 1, wherein one end of the input signal line is inserted by a length of $\lambda/4$ into the first waveguide, and one end of the output signal line is inserted by a length of $\lambda/4$ into the second waveguide.

5. The millimeter wave bands semiconductor package according to claim 1, wherein the first non-penetration hole is provided such that a bottom surface thereof is spaced upward by a length of $\lambda/4$ apart from the input signal line, and the second non-penetration hole is provided such that a bottom surface thereof is spaced upward by a length of $\lambda/4$ apart from the output signal line.

6. The millimeter wave bands semiconductor package according to claim 1, wherein a bias supplying line is further provided on the front side surface of the circuit board to supply a DC bias to a semiconductor chip, and

a region, which faces the bias supplying line, of a back side surface of the metal cover body is hollowed out so as to be shallower than the other region.

7. The millimeter wave bands semiconductor package according to claim 6, wherein a first ground pattern is provided on the front side surface of the circuit board, and

the first ground pattern is provided so as to be insulated from the input signal line, the output signal line, and the bias supplying line.

8. The millimeter wave bands semiconductor package according to claim 7, wherein the first ground pattern is not provided in the first waveguide and the second waveguide.

9. The millimeter wave bands semiconductor package according to claim 8, wherein a second ground pattern is provided on a back side surface of the circuit board so as to be electrically connected to the first ground pattern.

10. The millimeter wave bands semiconductor package according to claim 9, wherein the second ground pattern is provided on an entire surface of the back side surface of the circuit board excluding regions which are disposed in the first waveguide and the second waveguide.

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